

Data Sheet January 2000 File Number 3397.3

#### 30A, 1200V Ultrafast Diode

The RURP30120 is an ultrafast diode with soft recovery characteristic ( $t_{rr}$  < 110ns). It has low forward voltage drop and is silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristic minimize ringing and electrical noise in many power switching circuits, reducing power loss in the switching transistors.

Formerly developmental type TA49031.

### **Ordering Information**

PART NUMBER	PACKAGE	BRAND
RURP30120	TO-220AC	RUR30120

NOTE: When ordering, use the entire part number.

## Symbol



#### **Features**

•	Ultrafast with Soft Recovery <110ns
•	Operating Temperature
•	Reverse Voltage

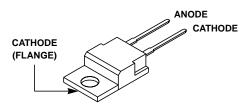
- Avalanche Energy Rated
- Planar Construction

### **Applications**

- Switching Power Supplies
- Power Switching Circuits
- · General Purpose

### **Packaging**

JEDEC TO-220AC



<b>Absolute Maximum Ratings</b> T <sub>C</sub> = 25°C, Unless Otherwise Specified		
	RURP30120	UNITS
Peak Repetitive Reverse VoltageV <sub>RRM</sub>	1200	V
Working Peak Reverse Voltage	1200	V
DC Blocking Voltage V <sub>R</sub>	1200	V
Average Rectified Forward Current	30	Α
Repetitive Peak Surge Current	60	Α
Nonrepetitive Peak Surge Current	300	Α
Maximum Power Dissipation	125	W
Avalanche Energy (See Figures 7 and 8)	30	mJ
Operating and Storage Temperature	-65 to 175	οС

**Electrical Specifications**  $T_C = 25^{\circ}C$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V <sub>F</sub>	I <sub>F</sub> = 30A	-	-	2.1	V
	$I_F = 30A, T_C = 150^{\circ}C$	-	-	1.9	V
I <sub>R</sub>	V <sub>R</sub> = 1200V	-	-	250	μΑ
	V <sub>R</sub> = 1200V, T <sub>C</sub> = 150°C	-	-	1	mA
t <sub>rr</sub>	$I_F = 1A$ , $dI_F/dt = 100A/\mu s$	-	-	110	ns
	I <sub>F</sub> = 30A, dI <sub>F</sub> /dt = 100A/μs	-	-	150	ns
t <sub>a</sub>	I <sub>F</sub> = 30A, dI <sub>F</sub> /dt = 100A/μs	-	90	-	ns
t <sub>b</sub>	I <sub>F</sub> = 30A, dI <sub>F</sub> /dt = 100A/μs	-	45	-	ns
$R_{ hetaJC}$		-	-	1.2	°C/W

#### **DEFINITIONS**

 $V_F$  = Instantaneous forward voltage (pw = 300 $\mu$ s, D = 2%).

 $I_R$  = Instantaneous reverse current.

 $t_{rr}$  = Reverse recovery time (See Figure 6), summation of  $t_a + t_b$ .

t<sub>a</sub> = Time to reach peak reverse current (See Figure 6).

 $t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 6).

 $R_{\theta JC}$  = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

# **Typical Performance Curves**

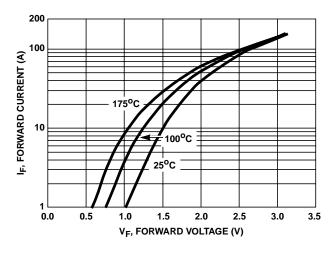


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

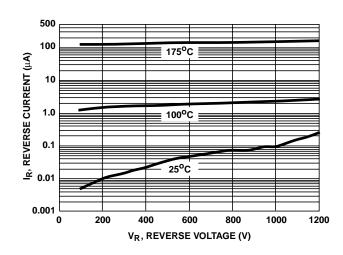


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

#### Typical Performance Curves (Continued)

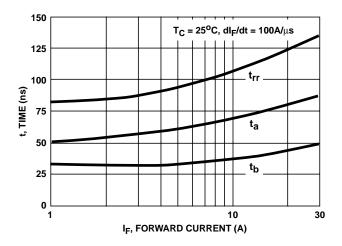


FIGURE 3. t<sub>rr</sub>, t<sub>a</sub> AND t<sub>b</sub> CURVES vs FORWARD CURRENT

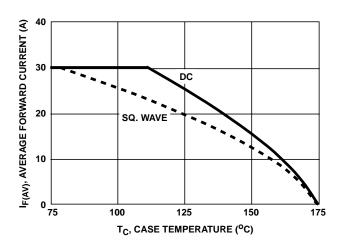


FIGURE 4. CURRENT DERATING CURVE

#### Test Circuits and Waveforms

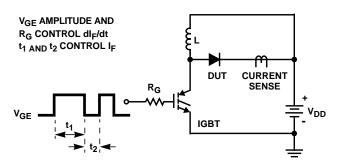


FIGURE 5. t<sub>rr</sub> TEST CIRCUIT

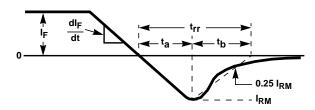


FIGURE 6. t<sub>rr</sub> WAVEFORMS AND DEFINITIONS

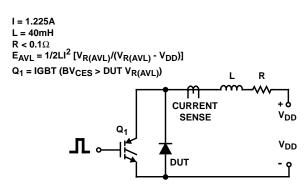


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

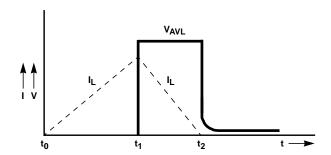


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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